## **General Description**

DIDT

The 831752 is a high-performance, differential HCSL clock switch. The device is designed for the routing of PCIe clock signals in ATCA/AMC system and is optimized for PCIe Gen 1, Gen 2 and Gen 3. The device has one differential, bi-directional I/O (FCLK) for connection to ATCA clock sources and to clock receivers through a connector. The differential clock input CLK is the local clock input and the HCSL output Q is the local clock output. In the common clock mode, FCLK serves as an input and is routed to the differential HCSL output Q. There are two local clock modes. In the local clock mode 0, CLK is the input, Q is the clock output and FCLK is in high-impedance state. In the local clock mode 1, CLK is the input and both Q and FCLK are the outputs of the locally generated PCIe clock signal. The 831752 is characterized to operate from a 3.3V power or 2.5V power supply. The 831752 supports the switching of PCI Express (2.5 Gb/s), Gen 2 (5 Gb/s) and Gen 3 (8 Gb/s) clock signals.

## Pin Assignment

DIR_SEL	1	16	IREF
nOEFCLK	2	15	GND
VDD	3	14	VDD
FCLK	4	13	Q
nFCLK	5	12	nQ
GND _	6	11	GND
CLK	7	10	VDD
nCLK	8	9	nc

831752 16-lead TSSOP 4.4mm x 5.0mm x 0.925mm package body G Package, Top View

## Features

- Clock switch for PCIe and ATCA/AMC applications
- Supports local and common ATCA/AMC clock modes
- Bi-directional clock I/O FCLK:
   When operating as an output, FCLK is a source-terminated HCSL signal.
  - When operating as an input, FCLK accepts HCSL, LVDS and LVPECL levels.
- Local clock input (CLK) accepts HCSL, LVDS and LVPECL differential signals
- Local HCSL clock output (Q)
- Maximum input/output clock frequency: 500MHz
- Maximum input/output data rate: 1000Mb/s (NRZ)
- LVCMOS interface levels for the control inputs
- PCI Express (2.5 Gb/S), Gen 2 (5 Gb/s) and Gen 3 (8 Gb/s) jitter compliant
- Full 3.3V or 2.5V supply voltage
- Lead-free (RoHS 6) 16-lead TSSOP package
- -40°C to 85°C ambient operating temperature



## **Block Diagram**

# Table 1. Pin Descriptions

Number	Name		Туре	Description
1	DIR_SEL	Input	Pulldown	Direction control for the FCLK I/O. Works in conjunction with nOEFCLK. See Table 3 for function. LVCMOS/LVTTL interface levels.
2	nOEFCLK	Input	Pullup	Output enable for the FCLK I/O output. Works in conjunction with DIR_SEL. See Table 3 for function. LVCMOS/LVTTL interface levels.
3, 10, 14	V <sub>DD</sub>	Power		Core and output power supply pin.
4, 5	FCLK, nFCLK	I/O		Differential I/O. Signal direction is controlled by DIR_SEL. Accepts differential signals when operating as an input. Differential HCSL signals when operating as an output. Internal source termination can be disabled. See Table 3 for function.
6, 11, 15	GND	Power		Power supply ground.
7	CLK	Input	Pulldown	Non-inverting input.
8	nCLK	Input	Pulldown/Pullup	Inverting differential clock input.
9	nc	Unused		No connect.
12, 13	nQ, Q	Output		Differential output pair. HCSL interface levels.
16	IREF	Input		An external fixed precision resistor ( $475\Omega$ ) from this pin to ground provides a reference current used for the differential current-mode Q and FCLK outputs.

NOTE: Pullup and pulldown refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

## **Table 2. Pin Characteristics**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance			4		pF
R <sub>PULLDOWN</sub>	Input Pulldown Resistor			51		kΩ
R <sub>PULLUP</sub>	Input Pullup Resistor			51		kΩ

## **Function Table**

### **Table 3. Direction Control Function Table**

Input	Input		
DIR_SEL	nOEFCLK	Operation	FCLK Function
0	0	Local clock mode 0. The input signal at CLK is routed to both outputs Q and FCLK.	Differential HCSL output with internal $50\Omega$ source termination
0 (default)	1 (default)	Local clock mode 1. The input signal at CLK is routed to the output Q.	Output is disabled (high impedance). Internal $50\Omega$ termination is disabled.
1	х	Common reference clock mode. FCLK is the clock input. Q is the clock output.	Differential clock input. Internal $50\Omega$ source termination is disabled as well as output driver and 22.33 $\Omega$ resistors.

NOTE: X = 0 or 1

## **Absolute Maximum Ratings**

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics or AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V <sub>DD</sub>	4.6V
Inputs, V <sub>I</sub>	-0.5V to V <sub>DD</sub> + 0.5V
Outputs, V <sub>O</sub>	-0.5V to V <sub>DD</sub> + 0.5V
Package Thermal Impedance, $\theta_{JA}$	81.2°C/W (0 mps)
Storage Temperature, T <sub>STG</sub>	-65°C to 150°C

## **DC Electrical Characteristics**

#### Table 4A. Power Supply DC Characteristics, $V_{DD}$ = 3.3V±5% or 2.5V±5%, $T_A$ = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V	Coro Supply Voltago		3.135	3.3	3.465	V
V <sub>DD</sub> Core Supply Vollage		2.375	2.5	2.625	V	
I <sub>DD</sub>	Power Supply Current				64	mA

#### Table 4B. LVCMOS/LVTTL DC Characteristics, $V_{DD}$ = 3.3V±5% or 2.5V±5%, $T_A$ = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V	/ <sub>IH</sub> Input High Voltage		$V_{DD} = 3.3V$	2		V <sub>DD</sub> + 0.3	V
⊻IH			$V_{DD} = 2.5 V$	1.7		V <sub>DD</sub> + 0.3	V
V	Input Low Voltage		V <sub>DD</sub> = 3.3V	-0.3		0.8	V
۷IL			V <sub>DD</sub> = 2.5V	-0.3		0.7	V
	DIR_SEL		DIR_SEL			150	μΑ
ЧН		nOEFLCK	$v_{DD} = v_{IN} = 2.025 v_{OI} 3.405 v_{OI}$			5	μA
	DIR_SEL			-5			μA
Input Low Current		nOEFLCK	$v_{DD} = 2.023 v_{OI} 3.403 v, v_{IN} = 0 v$	-150			μA

#### Table 4C. Differential DC Characteristics, $V_{DD}$ = 3.3V±5% or 2.5V±5%, $T_A$ = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
IIH	Input High Current	CLK, nCLK	$V_{DD} = V_{IN} = 3.3V$			150	μA
1	Input	CLK	$V_{DD} = 3.3V, V_{IN} = 0V$	-5			μA
ιL	Low Current	nCLK	$V_{DD} = 3.3V, V_{IN} = 0V$	-150			μA
V <sub>PP</sub>	Peak-to-Peak V	/oltage; NOTE 1		0.15		1.3	V
V <sub>CMR</sub>	Common Mode NOTE 1, 2	Input Voltage;		0.5		V <sub>DD</sub> – 0.85	V

NOTE 1: V<sub>IL</sub> should not be less than -0.3V.

NOTE 2: Common mode input voltage is defined as  $V_{IH}$ .

## **AC Electrical Characteristics**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	PCIe Industry Specification	Units
t <sub>j</sub> (PCle Gen 1)	Phase Jitter Peak-to-Peak; NOTE 1, 4	<i>f</i> = 100MHz Evaluation Band: 0Hz - Nyquist (clock frequency/2)		9.95	15.5	86	ps
t <sub>REFCLK_HF_RMS</sub> (PCIe Gen 2)	Phase Jitter RMS; NOTE 2, 4	f = 100MHz High Band: 1.5MHz - Nyquist (clock frequency/2)		0.82	1.12	3.1	ps
t <sub>REFCLK_LF_RMS</sub> (PCIe Gen 2)	Phase Jitter RMS; NOTE 2, 4	f = 100MHz Low Band: 10kHz - 1.5MHz		0.04	0.08	3.0	ps
<sup>t</sup> REFCLK_RMS (PCIe Gen 3)	Phase Jitter RMS; NOTE 3, 4	f = 100MHz Evaluation Band: 0Hz - Nyquist (clock frequency/2)		0.153	0.203	0.8	ps

Table 5A. PCI Express Jitter Specifications,  $V_{DD}$  = 3.3V±5% or 2.5V±5%,  $T_A$  = -40°C to 85°C

**NOTE:** Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions. For additional information, refer to the *PCI Express Application Note section* in the datasheet. **NOTE:** PCI Express Jitter Specifications apply to FCLK and nFCLK and Q, nQ operating as outputs. The source generator used in the PCI Express Jitter measurements is the Stanford Research Systems CG635 2.0GHz Synthesized Clock Generator.

**NOTE 1:** Peak-to-Peak jitter after applying system transfer function for the Common Clock Architecture. Maximum limit for PCI Express Gen 1 is 86ps peak-to-peak for a sample size of 10<sup>6</sup> clock periods.

**NOTE 2:** RMS jitter after applying the two evaluation bands to the two transfer functions defined in the Common Clock Architecture and reporting the worst case results for each evaluation band. Maximum limit for PCI Express Gen 2 is 3.1ps RMS for t<sub>REFCLK\_HF\_RMS</sub> (High Band) and 3.0ps RMS for t<sub>REFCLK\_LF\_RMS</sub> (Low Band).

**NOTE 3:** RMS jitter after applying system transfer function for the common clock architecture. This specification is based on the *PCI Express Base Specification Revision 0.7, October 2009* and is subject to change pending the final release version of the specification. **NOTE 4:** This parameter is guaranteed by characterization. Not tested in production.

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f <sub>OUT</sub>	Output Frequency			100	500	MHz
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Plot	100MHz, Integration Range: 12kHz – 20MHz		0.3	0.505	ps
		FCLK to Q	1.75		3.65	ns
t <sub>PD</sub>	Propagation Delay, NOTE 1	CLK to Q	1.95		3.90	ns
	-	CLK to FCLK	1.50		3.70	ns
MUXISOL	Mux Isolation	f = 100MHz		-70		dB
Edge Rate	Rise/Fall Edge Rate; NOTE 2, 3		0.6		4	V/ns
V <sub>RB</sub>	Ringback Voltage; NOTE 2, 4		-100		100	mV
t <sub>STABLE</sub>	Time before V <sub>RB</sub> is allowed; NOTE 2, 4		500			ps
V <sub>MAX</sub>	Absolute Max Output Voltage; NOTE 5, 6			800	1350	mV
V <sub>MIN</sub>	Absolute Min Output Voltage; NOTE 5, 7		-300	-35		mV
V <sub>CROSS</sub>	Absolute Crossing Voltage; NOTE 5, 8, 9		250	385	650	mV
$\Delta V_{CROSS}$	Total Variation of V <sub>CROSS</sub> over all edges; NOTE 5, 8, 10			40	140	mV
odo	Output Duty Cycle: NOTE 11	$f \leq 312.5 MHz$	44	50	56	%
ouc		f > 312.5MHz	40	50	60	

#### Table 5B. HCSL AC Characteristics, $V_{DD} = 3.3V \pm 5\%$ or 2.5V $\pm 5\%$ , $T_A = -40^{\circ}$ C to 85°C

**NOTE:** Measurements taken with Q output and FCLK output.

**NOTE:** Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: All measurements were taken with FCLK, nFCLK and Q, nQ operating as outputs unless otherwise noted.

NOTE 1: Measured from the differential input cross point to the differential output crossing point.

**NOTE 2:** Measurement taken from differential waveform.

**NOTE 3:** Measurement from -150mV to +150mV on the differential waveform (derived from Q minus nQ). The signal must be monotonic through the measurement region for rise and fall time. The 300mV measurement window is centered on the differential zero crossing. **NOTE 4:** T<sub>STABLE</sub> is the time the differential clock must maintain a minimum ±150mV differential voltage after rising/falling edges before it is allowed to drop back into the V<sub>RB</sub> ±100 differential range. See Parameter Measurement Information Section. **NOTE 5:** Measurement taken from single-ended waveform.

NOTE 6: Defined as the maximum instantaneous voltage including overshoot. See Parameter Measurement Information Section.

NOTE 7: Defined as the minimum instantaneous voltage including undershoot. See Parameter Measurement Information Section.

NOTE 8: Measured at crossing point where the instantaneous voltage value of the rising edge of Q equals the falling edge of nQ.

See Parameter Measurement Information Section.

**NOTE 9:** Refers to the total variation from the lowest crossing point to the highest, regardless of which edge is crossing. Refers to all crossing points for this measurement. See Parameter Measurement Information Section.

**NOTE 10:** Defined as the total variation of all crossing voltage of rising Q and falling nQ. This is the maximum allowed variance in the V<sub>CROSS</sub> for any particular system. See Parameter Measurement Information Section.

NOTE 11: Input duty cycle must be 50%.

**NOTE 12:** Matching applies to rising edge rate for Q and falling edge rate for nQ. It is measured using a ±75mV window centered on the median crosspoint where Q meets nQ falling. The median crosspoint is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The rise edge rate of Q should be compared to the fall edge rate of nQ, the maximum allowed difference should not exceed 20% of the slowest edge rate.

## **Parameter Measurement Information**



HCSL Output Load AC Test Circuit



Differential Measurement Points for Rise/Fall Edge Rate



Single-ended Measurement Points for Absolute Cross Point/Swing



### **Differential Input Levels**









# Parameter Measurement Information, continued





#### **Propagation Delay**



**Differential Measurement Points for Ringback** 

## **Applications Information**

### **Recommended Termination**



Figure 1. Interface for 831752I HCSL driver with built-in 50 ohm Termination to Receiver with High Input Impedance

### **Recommendations for Unused Input Pins**

### Inputs:

### **LVCMOS Control Pins**

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A  $1k\Omega$  resistor can be used.

### **CLK/nCLK Inputs**

For applications not requiring the use of the differential input, both CLK and nCLK can be left floating. Though not required, but for additional protection, a  $1k\Omega$  resistor can be tied from CLK to ground.

### FCLK/nFCLK Pins

In case FCLK/nFCLK are unused, one of the following two configurations can be used: either FCLK/nFCLK are configured as an output (DIR\_SEL = 1) and left floating, or FCLK/nFCLK are configured as an input (DIR\_SEL = 0). In this case 1k $\Omega$  pulldown is required on FCLK and 1k $\Omega$  Pullup is required on nFCLK.

### Wiring the Differential Input to Accept Single-Ended Levels

*Figure 2* shows how a differential input can be wired to accept single ended levels. The reference voltage  $V_1 = V_{DD}/2$  is generated by the bias resistors R1 and R2. The bypass capacitor (C1) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of R1 and R2 might need to be adjusted to position the V<sub>1</sub> in the center of the input voltage swing. For example, if the input clock swing is 2.5V and V<sub>DD</sub> = 3.3V, R1 and R2 value should be adjusted to set V<sub>1</sub> at 1.25V. The values below are for when both the single ended swing and V<sub>DD</sub> are at the same voltage. This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways. First, R3 and R4 in parallel should equal the transmission line impedance. For most 50 $\Omega$  applications, R3 and R4 can be 100 $\Omega$ . The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver. When using single-ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full rail LVCMOS signaling, it is recommended that the amplitude be reduced. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however V<sub>IL</sub> cannot be less than -0.3V and V<sub>IH</sub> cannot be more than V<sub>DD</sub> + 0.3V. Though some of the recommended components might not be used, the pads should be placed in the layout. They can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a differential signal.



Figure 2. Recommended Schematic for Wiring a Differential Input to Accept Single-ended Levels

### 3.3V Differential Clock Input Interface

The CLK/nCLK accepts HCSL, LVDS and LVPECL and other differential signals. Both differential signals must meet the V<sub>PP</sub> and V<sub>CMR</sub> input requirements. *Figures 2A to 2E* show interface examples for the CLK/nCLK input driven by the most common driver types. The input interfaces suggested here are examples only. If the driver is



Figure 3A. CLK/nCLK Input Driven by a 3.3V LVPECL Driver



Figure 3C. CLK/nCLK Input Driven by a 3.3V LVPECL Driver



Figure 3E. CLK/nCLK Input Driven by a 3.3V LVDS Driver

from another vendor, use their termination recommendation. Please consult with the vendor of the driver component to confirm the driver termination requirements. The figures below also apply to FCLK/ nFCLK operating as an input.



Figure 3B. CLK/nCLK Input Driven by a 3.3V HCSL Driver



Figure 3D. CLK/nCLK Input Driven by a 3.3V LVPECL Driver with AC Couple

### 2.5V Differential Clock Input Interface

The CLK/nCLK accepts HCSL, LVDS and LVPECL and other differential signals. Both differential signals must meet the V<sub>PP</sub> and V<sub>CMR</sub> input requirements. *Figures 4A to 4 E* show interface examples for the CLK/nCLK input driven by the most common driver types. The input interfaces suggested here are examples only. If the driver is



Figure 4A. CLK/nCLK Input Driven by a 2.5V LVPECL Driver



Figure 4C. CLK/nCLK Input Driven by a 2.5V LVPECL Driver



Figure 4E. CLK/nCLK Input Driven by a 2.5V LVDS Driver

from another vendor, use their termination recommendation. Please consult with the vendor of the driver component to confirm the driver termination requirements. The figures below also apply to FCLK/ nFCLK operating as an input.



Figure 4B. CLK/nCLK Input Driven by a 2.5V HCSL Driver



Figure 4D. CLK/nCLK Input Driven by a 2.5V LVPECL Driver with AC Couple

## **PCI Express Application Note**

PCI Express jitter analysis methodology models the system response to reference clock jitter. The block diagram below shows the most frequently used *Common Clock Architecture* in which a copy of the reference clock is provided to both ends of the PCI Express Link.

In the jitter analysis, the transmit (Tx) and receive (Rx) serdes PLLs are modeled as well as the phase interpolator in the receiver. These transfer functions are called H1, H2, and H3 respectively. The overall system transfer function at the receiver is:

 $Ht(s) = H3(s) \times [H1(s) - H2(s)]$ 

The jitter spectrum seen by the receiver is the result of applying this system transfer function to the clock spectrum X(s) and is:

 $Y(s) = X(s) \times H3(s) \times [H1(s) - H2(s)]$ 

In order to generate time domain jitter numbers, an inverse Fourier Transform is performed on X(s)\*H3(s) \* [H1(s) - H2(s)].



PCI Express Common Clock Architecture

For **PCI Express Gen 1**, one transfer function is defined and the evaluation is performed over the entire spectrum: DC to Nyquist (e.g for a 100MHz reference clock: OHz – 50MHz) and the jitter result is reported in peak-peak.



PCIe Gen 1 Magnitude of Transfer Function

For **PCI Express Gen 2**, two transfer functions are defined with 2 evaluation ranges and the final jitter number is reported in rms. The two evaluation ranges for PCI Express Gen 2 are 10kHz – 1.5MHz (Low Band) and 1.5MHz – Nyquist (High Band). The plots show the individual transfer functions as well as the overall transfer function Ht.







PCIe Gen 2B Magnitude of Transfer Function

### PCI Express Application Note.

For **PCI Express Gen 3**, one transfer function is defined and the evaluation is performed over the entire spectrum. The transfer function parameters are different from Gen 1 and the jitter result is reported in RMS.



PCle Gen 3 Magnitude of Transfer Function

For a more thorough overview of PCI Express jitter analysis methodology, please refer to IDT Application Note *PCI Express Reference Clock Requirements.* 

## **Power Considerations**

This section provides information on power dissipation and junction temperature for the 831752I. Equations and example calculations are also provided.

#### 1. Power Dissipation.

The total power dissipation for the 8317521 is the sum of the core power plus the analog power plus the power dissipated in the load(s). The following is the power dissipation for  $V_{DD} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

Power (core)<sub>MAX</sub> = V<sub>DD MAX</sub> \* I<sub>DD MAX</sub> = 3.465V \* 64mA = 221.76mW

Power dissipation for the FCLK, nFCLK input internal 50ohm termination. Assume the FCLK, nFCLK input is driven by a HCSL driver. Logic High input current ~ 17mA. Logic low current ~ 0mA.

Power (input) = 50ohm \* (17mA)<sup>2</sup> = 14.45mW

Total Power\_MAX (3.465V, with all outputs switching) = 221.76mW + 14.45mW = 236.21mW

#### 2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, Tj, to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for Tj is as follows: Tj =  $\theta_{JA}$  \* Pd\_total + T<sub>A</sub>

Tj = Junction Temperature

 $\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

Pd\_total = Total Device Power Dissipation (example calculation is in section 1 above)

T<sub>A</sub> = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is 81.2°C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 85°C with all outputs switching is:

 $85^{\circ}C + 0.236W * 81.2^{\circ}C/W = 104.2^{\circ}C$ . This is below the limit of  $125^{\circ}C$ .

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

#### Table 6. Thermal Resistance $\theta_{JA}$ for 16 Lead TSSOP, Forced Convection

$\theta_{JA}$ vs. Air Flow					
Meters per Second	0	1	2.5		
Multi-Layer PCB, JEDEC Standard Test Boards	81.2°C/W	73.9°C/W	70.2°C/W		

## **Package Outline and Package Dimensions**

### Table 7. $\theta_{JA}$ vs. Air Flow Table for a 16 Lead TSSOP

θ <sub>JA</sub> vs. Air Flow					
Meters per Second	0	1	2.5		
Multi-Layer PCB, JEDEC Standard Test Boards	81.2°C/W	73.9°C/W	70.2°C/W		

### **Transistor Count**

The transistor count for 831752l is: 446

## Package Outline and Package Dimensions

Package Outline - G Suffix for 16 Lead TSSOP



#### Table 8. Package Dimensions for 16 Lead TSSOP

All Dimensions in Millimeters					
Symbol	Minimum	Maximum			
N	16				
Α		1.20			
A1	0.05	0.15			
A2	0.80	1.05			
b	0.19	0.30			
С	0.09	0.20			
D	4.90	5.10			
Е	6.40 Basic				
E1	4.30	4.50			
е	0.65 Basic				
L	0.45	0.75			
α	0°	8°			
aaa		0.10			

Reference Document: JEDEC Publication 95, MO-153

# **Ordering Information**

### Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
831752AGILF	31752AIL	Lead-Free, 16-lead TSSOP	Tube	-40°C to 85°C
831752AGILFT	31752AIL	Lead-Free, 16-lead TSSOP	Tape & Reel	-40°C to 85°C

# **Revision History Sheet**

Rev	Table	Page	Description of Change	Date
A	9	15	Ordering Information Table - corrected marking	12/20/13
A			Removed ICS from part number where needed. Updated header and footer.	4/5/16
В		1	Block Diagram - corrected labels. Deleted "I" suffix from part number.	6/28/16



Corporate Headquarters 6024 Silver Creek Valley Road San Jose, CA 95138 USA www.IDT.com

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